

D'wel

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film, wherein said conductive layer and said second metallic layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film.

Sub F2

7. (Twice Amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a thin film transistor;

a first metallic layer formed on said first insulating film;

a second metallic layer formed on said first metallic layer;

D2

a second insulating film formed on said second metallic layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film, wherein a source region or a drain region of said thin film transistor and said second metallic layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film.

Sub F3

19. (Twice Amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a thin film transistor;

a first conductive layer formed on said first insulating film;

D3

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film,

wherein said second conductive layer is in contact with said first insulating film inside of said contact holes.

D3
incl

28. (Twice Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first insulating film.

D4

34. (Twice Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

sub 2

D5

Sub
F6
D5
level

a second conductive layer formed on said first conductive layer;
a second insulating film formed on said second conductive layer; and
a pixel electrode formed on said second insulating film, said pixel electrode being connected
to said second conductive layer through a contact hole provided in said second insulating film,
wherein said second conductive layer is directly connected to said semiconductor layer
through a contact hole provided in said first conductive layer and said first insulating film.

Sub
F6

D6

40. (Amended) A semiconductor device comprising:
a thin film transistor formed over a substrate, said thin film transistor having a semiconductor
layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed
therebetween;
a first insulating film formed over said thin film transistor;
a first wiring formed on said first insulating film;
a second wiring formed on said first wiring;
a second insulating film formed on said second wiring; and
a pixel electrode formed on said second insulating film, said pixel electrode being connected
to said second wiring through a contact hole provided in said second insulating film,
wherein said second wiring is directly connected to said semiconductor layer through a
contact hole provided in said first insulating film.

REMARKS

The following remarks are in response to the Examiner's comments in the Advisory Action
and rejections in the Final Rejection